

DIGITAL TV TUNER IC

Check for Samples: SN761645

FEATURES

- Integrated Mixer/Oscillator/PLL and IF GCA
- VHF-L, VHF-H, UHF 3-Band Local Oscillator
- RF AGC Detector Circuit
- I2C Bus Protocol
- Seven-Step Charge Pump Current
- Four NPN Emitter-Follower Type Band Switch
 Drivers
- One Auxiliary Port/5-Level ADC
- Programmable Reference Divider Ratio
- Crystal Oscillator 4-MHz/16-MHz Support
- Selectable Digital IFOUT and Analog IFOUT
- Standby Mode
- 5-V Power Supply
- 38-Pin TSSOP Package

APPLICATIONS

- Digital TV
- Digital CATV
- Set-Top Box

DESCRIPTION

The SN761645 is a low-phase-noise synthesized tuner IC designed for digital TV tuning systems. The circuit consists of a PLL synthesizer, three-band local oscillator and mixer, RF AGC detector circuit, and IF gain controlled amplifier, and is available in a small outline package.

IF GCA OUT2 🖂

IF GCA OUT1

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ORDERING INFORMATION

For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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21 XTAL2

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☐ XTAL1



TEXAS INSTRUMENTS

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UHF OSC UHF OSC 2 IF IN HIXOUT 1 H VHI OSC _ Ū Ð ÷ IF AMP + ╡ DIFOUT1 VHF-L VHF-H UHF **DIFOUT 2** OSC OSC OSC AIFOUT Ľ Ċ, IF GND VHF-L VHF-H UHF VLO RF IN Г MIXER MIXER MIXER Þ VHI RF IN RF AGC OUT Ľ **RF AGC** UHF RF IN 1 Þ DETECT UHF RF IN 2 RF GND ¢ PROGRAMMABLE DIVIDER CP 'n VTU XTAL 1/1,1/4 REFERENCE PHASE CHARGE OP XTAL 1 Г OSC DIV DIVIDER DETECTOR PUMP AMP XTAL 2 ģ VCC NPN SWITCH PORT I2C BUS IF GCA OUT1 Ċ SCL IF INTERFACE GCA SDA ģ IF GCA OUT2 AS Ċ. \$ # چ س IF GCA GND 1 5-LEVEL BUS GND ¢ ADC Ò ·D ŀ IF GCA IN2 BS 4 P5/ADC BS 3 BS 2 BS 1 IF GCA CTRL

FUNCTIONAL BLOCK DIAGRAM

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TERMINAL FUNCTIONS

TERMINAL		DESCRIPTION	SCHEMATIC
NAME	NO.		
AIF OUT	9	IF amplifier output (unbalanced)	Figure 1
AS	22	Address selection input (open or connection to GND)	Figure 2
BS1	25	Band-switch 1 output (emitter follower)	Figure 3
BS2	26	Band-switch 2 output (emitter follower)	Figure 3
BS3	27	Band-switch 3 output (emitter follower)	Figure 3
BS4	38	Band-switch 4 output (emitter follower)	Figure 3
BUS GND	29	BUS ground	
CP	6	Charge pump output	Figure 4
DIF OUT1	10	IF amplifier balance output 1	Figure 5
DIF OUT2	11	IF amplifier balance output 2	Figure 5
IF GCA CTRL	16	IF GCA control voltage input	Figure 6
IF GCA GND	17	IF GCA ground	
IF GCA IN1	14	IF GCA input 1	Figure 7
IF GCA IN2	15	IF GCA input 2	Figure 7
IF GCA OUT1	19	IF GCA output 1	Figure 8
IF GCA OUT2	18	IF GCA output 2	Figure 8
IF GND	8	IF ground	
IF IN	30	IF amplifier input	Figure 9
MIX OUT1	31	Mixer output 1	Figure 10
MIX OUT2	32	Mixer output 2	Figure 10
OSC GND	5	Oscillator ground	
P5/ADC	12	Port-5 output/ADC input	Figure 11
RF AGC OUT	28	RF AGC output	Figure 12
RF GND	33	RF ground	
SCL	23	Serial clock input	Figure 13
SDA	24	Serial data input/output	Figure 14
UHF OSC1	3	UHF oscillator 1	Figure 15
UHF OSC2	4	UHF oscillator 2	Figure 15
UHF RF IN1	37	UHF RF input 1	Figure 16
UHF RF IN2	36	UHF RF input 2	Figure 16
VCC	13	Supply voltage	
VHI OSC	2	VHF HIGH oscillator	Figure 17
VHI RF IN	35	VHF HIGH RF input	Figure 18
VLO OSC	1	VHF LOW oscillator	Figure 19
VLO RF IN	34	VHF LOW RF input	Figure 20
VTU	7	Tuning voltage amplifier output	Figure 21
XTAL1	20	Crystal oscillator	Figure 22
XTAL2	21	Crystal oscillator	Figure 22

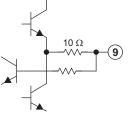


Figure 1. AIF OUT

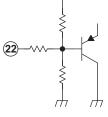


Figure 2. AS



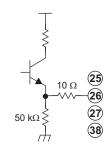
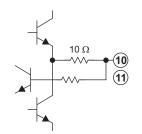
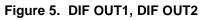


Figure 3. BS1, BS2, BS3, BS4





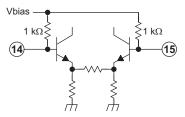
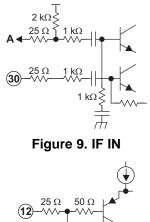
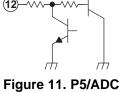


Figure 7. IF GCA IN1, IF GCA IN2





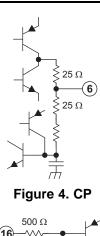


Figure 6. IF GCA CTRL

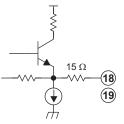


Figure 8. IF GCA OUT1, IF GCA OUT2

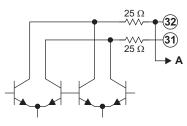


Figure 10. MIXOUT1, MIXOUT2

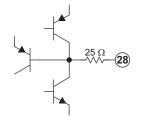
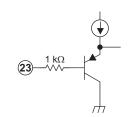
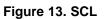


Figure 12. RF AGC OUT







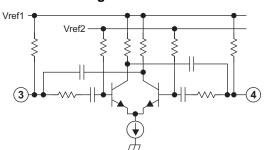
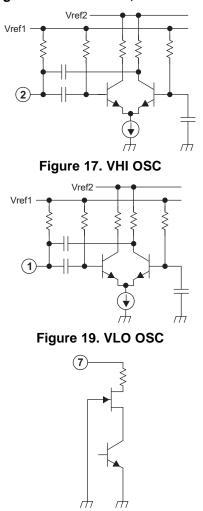


Figure 15. UHF OSC 1, UHF OSC 2





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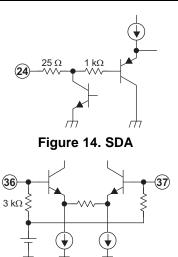


Figure 16. UHF RF IN1, UHF RF IN2

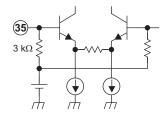


Figure 18. VHI RF IN

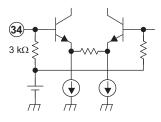


Figure 20. VLO RF IN

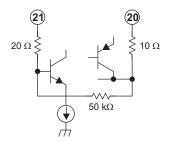


Figure 22. XTAL1, XTAL2

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EXAS

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

over recommended operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range ⁽²⁾	V _{cc}	-0.4	6.5	V
V _{GND}	Input voltage range 1 ⁽²⁾	RF GND, OSC GND, BUS GND	-0.4	0.4	V
VTU	Input voltage range 2 ⁽²⁾	VTU	-0.4	35	V
V _{IN}	Input voltage range 3 ⁽²⁾	Other pins	-0.4	6.5	V
P _D	Continuous total dissipation (3)	T _A ≤ 25°C		1277	mW
T _A	Operating free-air temperature range		-20	85	°C
T _{stg}	Storage temperature range		-65	150	°C
TJ	Maximum junction temperature			150	°C
t _{SC(max}	Maximum short-circuit time	Each pin to V_{CC} or to GND		10	S

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) Voltage values are with respect to the IF GND of the circuit.

(3) Derating factor is 10.2 mW/°C for $T_A > 25^{\circ}C$.

RECOMMENDED OPERATING CONDITIONS

			MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage	V _{CC}	4.5	5	5.3	V
VTU	Tuning supply voltage	VTU		30	33	V
I_{BS}	Output current of band switch	BS1 to BS4, one band switch on			10	mA
I_{P5}	Output current of port 5	P5			-5	mA
T _A	Operating free-air temperature		-20		85	°C



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

IF IN1, MIX OUT 1, and MIX OUT 2 (pins 30, 31, and 32, respectively) withstand 1.5 kV, and all other pins withstand 2 kV, according to the Human-Body Model (1.5 k Ω , 100 pF).

ELECTRICAL CHARACTERISTICS

Total Device and Serial Interface

 $V_{CC} = 4.5$ V to 5.3 V, $T_A = -20^{\circ}$ C to 85°C (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _{CC} 1	Supply current 1	BS[1:4] = 0100, IFGCA disabled		90		mA
I _{CC} 2	Supply current 2	BS[1:4] = 0100, IFGCA enabled		110		mA
I _{CC-STBY}	Standby supply current	BS[1:4] = 1100		9		mA
V _{IH}	High-level input voltage (SCL, SDA)		2.3			V
V _{IL}	Low-level input voltage (SCL, SDA)				1.05	V
I _{IH}	High-level input current (SCL, SDA)				10	μA
IIL	Low-level input current (SCL, SDA)		-10			μA
V _{POR}	Power-on-reset supply voltage (threshold of supply voltage between reset and operation mode)		2.1	2.8	3.5	V
I ² C Interfa	ice					
V _{ADC}	ADC input voltage	See Table 11	0		V _{CC}	V
I _{ADH}	ADC high-level input current	$V_{ADC} = V_{CC}$			10	μA
I _{ADL}	ADC low-level input current	V _{ADC} = 0 V	-10			μA
V _{OL}	Low-level output voltage (SDA)	V _{CC} = 5 V, I _{OL} = 3 mA			0.4	V
I _{SDAH}	High-level output leakage current (SDA)	V _{SDA} = 5.3 V			10	μA
f _{SCL}	Clock frequency (SCL)			100	400	kHz
t _{HD-DAT}	Data hold time	See Figure 23	0		3.45	μs
t _{BUF}	Bus free time		1.3			μs
t _{HD-STA}	Start hold time		0.6			μs
t _{LOW}	SCL-low hold time		1.3			μs
t _{HIGH}	SCL-high hold time		0.6			μs
t _{SU-STA}	Start setup time		0.6			μs
t _{SU-DAT}	Data setup time		0.1			μs
t _r	Rise time (SCL, SDA)				1	μs
t _f	Fall time (SCL, SDA)				0.3	μs
t _{SU-STO}	Stop setup time		0.6			μs

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PLL and Band Switch

 V_{CC} = 4.5 V to 5.3 V, T_A = -20°C to 85°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
N	Divider ratio	15-bit frequency word	512		32767	
f _{XTAL}	Crystal oscillator frequency	$R_{XTAL} = 25 \Omega$ to 300 Ω		4	16	MHz
Z _{XTAL}	Crystal oscillator input impedance	4-MHz crystal, V_{CC} = 5 V, T_A = 25°C		2		kΩ
V _{VTUL}	Tuning amplifier low-level output voltage	$R_L = 20 \text{ k}\Omega, \text{ VTU} = 33 \text{ V}$	0.2	0.45	0.6	V
I _{VTUOFF}	Tuning amplifier leakage current	Tuning amplifier = off, VTU = 33 V			10	μA
I _{CP000}		CP[2:0] = 000		35		
I _{CP001}		CP[2:0] = 001		70		
I _{CP010}		CP[2:0] = 010		140		
I _{CP011}	Charge-pump current	CP[2:0] = 011		210		μA
I _{CP100}		CP[2:0] = 100		280		
I _{CP101}		CP[2:0] = 101		350		
I _{CP110}		CP[2:0] = 110		420		
V _{CP}	Charge-pump output voltage	PLL locked		1.95		V
I _{CPOFF}	Charge-pump leakage current	V _{CP} = 2 V, T _A = 25°C	-15		15	nA
I _{BS}	Band switch driver output current (BS1–BS4)				10	mA
V _{BS1}	Dend switch driver systems unknow (DC4, DC4)	I _{BS} = 10 mA	2.9			N
V _{BS2}	Band switch driver output voltage (BS1–BS4)	I_{BS} = 10 mA, V_{CC} = 5 V, T_A = 25°C	3.4	3.6		V
IBSOFF	Band switch driver leakage current (BS1-BS4)	V _{BS} = 0 V			8	μA
I _{P5}	Band switch port sink current (P5/ADC)		-5			mA
V _{P5ON}	Band switch port output voltage (P5/ADC)	I _{P5} = -2 mA, V _{CC} = 5 V, T _A = 25°C			0.6	V

RF AGC⁽¹⁾

 V_{CC} = 5 V, T_A = 25°C, measured in Figure 24 reference measurement circuit at 50- Ω system, IF = 36.15 MHz (unless otherwise noted)

PARAMETER		ТІ	TEST CONDITIONS			MAX	UNIT
I _{OAGC0}		ATC = 0	ATC = 0		300		nA
I _{OAGC1}	RF AGC output source current	ATC = 1			9		μA
I_{OAGCSINK}	RF AGC peak sink current	ATC = 0			100		μA
VOAGCH	RFAGCOUT output high voltage (max level)	ATC = 1		3.7	4.2	4.7	V
VOAGCL	RFAGCOUT output low voltage (min level)	ATC = 1			0.3		V
V _{AGCSP00}			ATP[2:0] = 000		114		
V _{AGCSP01}			ATP[2:0] = 001		112		
V _{AGCSP02}			ATP[2:0] = 010		110		
V _{AGCSP03}	Start-point IF output level	AISL = 0	ATP[2:0] = 011		108		dBµV
V _{AGCSP04}			ATP[2:0] = 100		106		
V _{AGCSP05}			ATP[2:0] = 101		104		
V _{AGCSP06}			ATP[2:0] = 110		102		

(1) When AISL = 1, RF AGC function is not available at VHF-L band.



Mixer, Oscillator, IF Amplifier (DIF OUT)

 V_{CC} = 5 V, T_A = 25°C, measured in Figure 24 reference measurement circuit at 50- Ω system, IF = 36.15 MHz (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN TYP MAX	UNIT
GC _{1D}		f _{IN} = 50.85 MHz ⁽¹⁾	35	dB
GC _{3D}	Conversion gain (mixer - IF amplifier), VHF-LOW	f _{IN} = 149.85 MHz ⁽¹⁾	35	dB
GC _{4D}		f _{IN} = 156.85 MHz ⁽¹⁾	35	dB
GC _{6D}	Conversion gain (mixer - IF amplifier), VHF-HIGH	f _{IN} = 425.85 MHz ⁽¹⁾	35	dB
GC _{7D}		f _{IN} = 433.85 MHz ⁽¹⁾	35	dB
GC _{9D}	Conversion gain (mixer - IF amplifier), UHF	f _{IN} = 857.85 MHz ⁽¹⁾	35	dB
NF_{1D}		f _{IN} = 50.85 MHz	9	dB
NF_{3D}	Noise figure, VHF-LOW	f _{IN} = 149.85 MHz	9	dB
NF_{4D}		f _{IN} = 156.85 MHz	9	dB
NF _{6D}	Noise figure, VHF-HIGH	f _{IN} = 425.85 MHz	10	dB
NF _{7D}		f _{IN} = 433.85 MHz	10	dB
NF _{9D}	- Noise figure, UHF	f _{IN} = 857.85 MHz	11	dB
CM _{1D}	Input voltage causing 1% cross modulation distortion,	f _{IN} = 50.85 MHz ⁽²⁾	92	dBµV
CM _{3D}	VHF-LOW	f _{IN} = 149.85 MHz ⁽²⁾	92	dBµV
$\rm CM_{4D}$	Input voltage causing 1% cross modulation distortion,	f _{IN} = 156.85 MHz ⁽²⁾	92	dBµV
CM _{6D}	VHF-HIGH	f _{IN} = 425.85 MHz ⁽²⁾	92	dBµV
CM _{7D}	Input voltage equaing 10/ grace modulation distortion 1111	f _{IN} = 433.85 MHz ⁽²⁾	92	dBµV
CM _{9D}	Input voltage causing 1% cross modulation distortion, UHF	f _{IN} = 857.85 MHz ⁽²⁾	92	dBµV
V _{IFO1D}		f _{IN} = 50.85 MHz	117	dBµV
V _{IFO3D}	IF output voltage, VHF-LOW	f _{IN} = 149.85 MHz	117	dBµV
V _{IFO4D}	IF output voltage, VHF-HIGH	f _{IN} = 156.85 MHz	117	dBµV
V _{IFO6D}	ir ouput voltage, vnr-nign	f _{IN} = 425.85 MHz	117	dBµV
V _{IFO7D}	IF output voltage, UHF	f _{IN} = 433.85 MHz	117	dBµV
V _{IFO9D}	ir ouput voltage, onr	f _{IN} = 857.85 MHz	117	dBµV
Φ_{PLVL1D}	Phase noise, VHF-LOW	f _{IN} = 50.85 MHz ⁽³⁾	-92	dBc/Hz
Φ_{PLVL3D}		f _{IN} = 149.85 MHz ⁽⁴⁾	-91	dBc/Hz
Φ_{PLVL4D}		f _{IN} = 156.85 MHz ⁽³⁾	-86	dBc/Hz
Φ_{PLVL6D}	Phase noise, VHF-HIGH	f _{IN} = 425.85 MHz ⁽⁴⁾	-83	dBc/Hz
Φ_{PLVL7D}	Phase noise, UHF	f _{IN} = 433.85 MHz ⁽³⁾	-79	dBc/Hz
Φ_{PLVL9D}		f _{IN} = 857.85 MHz ⁽⁴⁾	-77	dBc/Hz

(1) RF input level = 70 dB μ V, differential output (2) $f_{undes} = f_{des} \pm 7$ MHz, Pin = 70 dB μ V, AM 1 kHz, 30%, DES/CM = S/I = 46 dB (3) Offset = 1 kHz, CP current = 70 μ A, reference divider = 24 (4) Offset = 1 kHz, CP current = 420 μ A, reference divider = 24

otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN TYP MAX	UNIT
GC _{1A}	Conversion agin (miver, JE emplifier) \//JE LOW	f _{IN} = 50.85 MHz ⁽¹⁾	29	dB
GC _{3A}	Conversion gain (mixer - IF amplifier), VHF-LOW	f _{IN} = 149.85 MHz ⁽¹⁾	29	dB
GC _{4A}		f _{IN} = 156.85 MHz ⁽¹⁾	29	dB
GC _{6A}	Conversion gain (mixer - IF amplifier), VHF-HIGH	f _{IN} = 425.85 MHz ⁽¹⁾	29	dB
GC _{7A}		f _{IN} = 433.85 MHz ⁽¹⁾	29	dB
GC _{9A}	Conversion gain (mixer - IF amplifier), UHF	f _{IN} = 857.85 MHz ⁽¹⁾	29	dB
NF _{1A}		f _{IN} = 50.85 MHz	9	dB
NF _{3A}	Noise figure, VHF-LOW	f _{IN} = 149.85 MHz	9	dB
NF _{4A}	Noise figure, VHF-HIGH	f _{IN} = 156.85 MHz	9	dB
NF _{6A}		f _{IN} = 425.85 MHz	10	dB
NF _{7A}	Noise figure, UHF	f _{IN} = 433.85 MHz	10	dB
NF _{9A}	Noise ligure, of li	f _{IN} = 857.85 MHz	11	dB
CM _{1A}	Input voltage causing 1% cross modulation distortion,	$f_{IN} = 50.85 \text{ MHz}^{(2)}$	87	dBµV
CM _{3A}	VHF-LOW	f _{IN} = 149.85 MHz ⁽²⁾	87	dBµV
CM _{4A}	Input voltage causing 1% cross modulation distortion,	$f_{IN} = 156.85 \text{ MHz}^{(2)}$	87	dBµV
CM _{6A}	VHF-HIGH	f $_{\rm IN}$ = 425.85 MHz $^{(2)}$	87	dBµV
CM _{7A}	Input voltage causing 1% cross modulation distortion, UHF	$f_{IN} = 433.85 \text{ MHz}^{(2)}$	87	dBµV
CM _{9A}	Input voltage causing 1% cross modulation distortion, OHP	f $_{\rm IN}$ = 857.85 MHz $^{(2)}$	87	dBµV
V _{IFO1A}		f _{IN} = 50.85 MHz	117	dBµV
V _{IFO3A}	IF output voltage, VHF-LOW	f _{IN} = 149.85 MHz	117	dBµV
V _{IFO4A}	IF output voltage, VHF-HIGH	f _{IN} = 156.85 MHz	117	dBµV
V _{IFO6A}	ir ouput voltage, vrir-riigir	f _{IN} = 425.85 MHz	117	dBµV
V _{IFO7A}	IF output voltage. UHF	f _{IN} = 433.85 MHz	117	dBµV
V _{IFO9A}	IF oulput voltage, OFF	f _{IN} = 857.85 MHz	117	dBµV
Φ _{PLVL1A}		f _{IN} = 50.85 MHz ⁽³⁾	-92	dBc/Hz
⊅ _{PLVL3A}	Phase noise, VHF-LOW	f _{IN} = 149.85 MHz ⁽³⁾	-96	dBc/Hz
⊅ _{PLVL4A}		f _{IN} = 156.85 MHz ⁽³⁾	-85	dBc/Hz
⊅ _{PLVL6A}	Phase noise, VHF-HIGH	f _{IN} = 425.85 MHz ⁽³⁾	-88	dBc/Hz
⊅ _{PLVL7A}		f _{IN} = 433.85 MHz ⁽³⁾	-80	dBc/Hz
Φ _{PLVL9A}	Phase noise, UHF	f _{IN} = 857.85 MHz ⁽³⁾	-85	dBc/Hz

 V_{CC} = 5 V, T_A = 25°C, measured in Figure 24 reference measurement circuit at 50- Ω system, IF = 36.15 MHz (unless

(1) RF input level = 70 dB μ V

 $f_{undes} = f_{des} \pm 7$ MHz, Pin = 70 dBµV, AM 1 kHz, 30%, DES/CM = S/I = 46 dB Offset = 10 kHz, CP current = 35 µA, reference divider = 64 (2) (3)

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Mixer, Oscillator, IF Amplifier (AIF OUT)





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IF Gain Controlled Amplifier

 $V_{CC} = 5 \text{ V}, T_A = 25^{\circ}\text{C}$, measured in Figure 24 reference measurement circuit at 50- Ω system, IF = IF = 36.15 MHz (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _{IFGCA}	Input current (IF GCA CTRL)	V _{IFGCA} = 3 V		60	90	μA
VIFGCAMAX	Maximum gain control voltage	Gain maximum	3		V_{CC}	V
VIFGCAMIN	Minimum gain control voltage	Gain minimum	0		0.2	V
GIFGCAMAX	Maximum gain	V _{IFGCA} = 3 V		67		dB
GIFGCAMIN	Minimum gain	V _{IFGCA} = 0 V		3		dB
GCR _{IFGCA}	Gain control range	$V_{IFGCA} = 0 V \text{ to } 3 V$		64		dB
VIFGCAOUT	Output voltage	Single-ended output, $V_{IFGCA} = 3 V$				Vpp
NFIFGCA	Noise figure	V _{IFGCA} = 3 V		11		dB
IM3 _{IFGCA}	Third order intermodulation distortion	$ f_{IFGCAIN1} = 35.65 \text{ MHz}, \\ f_{IFGCAIIN2} = 36.65 \text{ MHz}, \\ V_{IFGCAOUT} = -2 \text{ dBm}, \\ V_{IFGCA} = 3 \text{ V} $		-50		dBc
IIP _{3IFGCA}	Input intercept point	V _{IFGCA} = 0 V		11		dBm
RIFGCAIN	Input resistance (IF GCA IN1, IF GCA IN2)			1		kΩ
RIFGCAOUT	Output resistance (IF GCA OUT1, IF GCA OUT2)			25		Ω



FUNCTIONAL DESCRIPTION

I²C Bus Mode

I^2C Write Mode (R/W = 0)

			à					à	
	MSB							LSB	
Address Byte (ADB)	1	1	0	0	0	0	MA	R/W = 0	A ⁽¹⁾
Divider Byte 1 (DB1)	0	N14	N13	N12	N11	N10	N9	N8	A ⁽¹⁾
Divider Byte 2 (DB2)	N7	N6	N5	N4	N3	N2	N1	N0	A ⁽¹⁾
Control Byte 1 (CB1)	1	0	ATP2	ATP1	ATP0	RS2	RS1	RS0	A ⁽¹⁾
Band Switch Byte (BB)	CP1	CP0	AISL	P5	BS4	BS3	BS2	BS1	A ⁽¹⁾
Control Byte 2 (CB2)	1	1	ATC	MODE	DISGCA	IFDA	CP2	IXD4	A ⁽¹⁾

Table 1. Write Data Format

(1) A = acknowledge

Table 2. Write Data Symbol Description

SYMBOL	DESCRIPTION	DEFAULT
	Address set bit	
MA	MA = 0: AS pin = 0 V (connection to GND)	
	MA = 1 : AS pin = Open	
N[14.0]	Programmable counter set bits	N14 = N13 = N12 = = N0 = 0
N[14:0]	N = N14 x 2 ¹⁴ + N13 x 2 ¹³ + + N1 x 2 + N0	N14 = N13 = N12 = = N0 = 0
ATP[2:0]	RF AGC start-point control bits (see Table 3)	ATP[2:0] = 000
RS[2:0]	Reference divider ratio-selection bits (see Table 4)	RS[2:0] = 000
CP[2:0]	Charge-pump current set bits (see Table 5)	CP[2:0] = 000
	Port output / ADC input control bit	
P5	P5 = 0: ADC input	P5 = 0
	P5 = 1 : Tr = ON	
	Band-switch driver output control bits	
	BSn = 0: Tr = OFF	
	BSn = 1: Tr = ON	
	Band selection and standby function control bits	
BS[4:1]	BS2 BS1	BS[4:1] = 0000
	0 1 VHF-LO	
	1 0 VHF-HI	
	0 0 UHF	
	1 1 Standby mode / stop MOP function	
	RFAGC output current-set bit	
ATC	ATC = 0: Source current = 300nA	ATC = 0
	ATC = 1: Source current = 9uA	
	Device mode selection bit	
MODE	MODE = 0 : Test mode	MODE = 0
	MODE = 1 : Normal operation	
	Other control bits	
DISGCA	DISGCA IF GCA control bit (see Table 6)	DISGCA = 0
IFDA	IFDA AIF/DIF OUT selection bit (see Table 7)	IFDA = 0
AISL	AISL RFAGC detector input selection bit (see Table 8)	AISL = 0
IXD4	IXD4 Reference divider control bit (see Table 4)	IXD4 = 0

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NODE	A TD0		4700	IFOUT LEVEL		
MODE	ATP2	ATP1	ATP0	(dBµV)	(mVp-p)	
1	0	0	0	114	1417	
1	0	0	1	112	1126	
1	0	1	0	110	894	
1	0	1	1	108	710	
1	1	0	0	106	564	
1	1	0	1	104	448	
1	1	1	0	102	356	
1	1	1	1	Disabled		

Table 3. RF AGC Start Point

Table 4. Reference Divider Ratio

MODE	IXD4	RS2	RS1	RS0	REFERENCE DIVIDER RATIO
1	0	0	0	0	96
1	0	0	0	1	112
1	0	0	1	0	128
1	0	0	1	1	256
1	0	1	0	0	512
1	0	1	0	1	320
1	1	0	0	0	24
1	1	0	0	1	28
1	1	0	1	0	32
1	1	0	1	1	64
1	1	1	0	0	128
1	1	1	0	1	80
1	Х	1	1	1	Forbidden

Table 5. Charge-Pump Current

MODE	CP2	CP1	CP0	CHARGE PUMP CURRENT (µA)
1	0	0	0	35
1	0	0	1	70
1	0	1	0	140
1	0	1	1	210
1	1	0	0	280
1	1	0	1	350
1	1	1	0	420
1	1	1	1	Forbidden

Table 6. IF GCA Control

MODE	DISGCA	IF GCA FUNCTION
1	0	IF GCA enabled
1	1	IF GCA disabled

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Table 7. AIF / DIF OUT Selection

MODE	IFDA	IF OUT FUNCTION
1	0	DIF OUT 1,2 selected
1	1	AIF OUT selected

Table 8. RF AGC Detector Input Selection

MODE	AISL	RF AGC DETECTOR INPUT
1	0	IF amplifier selected
1	1 ⁽¹⁾	Mixer selected

(1) When AISL = 1, RF AGC function is not available at VHF-L band (output level is undefined).

I^2C Read Mode (R/W = 1)

Table 9. Read Data Format

	MSB							LSB	
Address byte (ADB)	1	1	0	0	0	0	MA	R/W = 1	A ⁽¹⁾
Status byte (SB)	POR	FL	1	1	1	A2	A1	A0	-

(1) A = acknowledge

Table 10. Read Data Symbol Description

SYMBOL	DESCRIPTION	DEFAULT
MA	Address set bit	
	MA = 0 : VLO OSC/AS pin = 0 V (connection to GND)	
	MA = 1 : VLO OSC/AS pin = Open	
POR	Power-on-reset flag	POR = 1
	POR set: power on POR reset: end-of-data transmission procedure	
FL	In-lock flag ⁽¹⁾	
	FL = 0 : PLL unlocked	
	FL = 1 : PLL locked	
A[2:0]	Digital data of ADC (see Table 11)	
	Bit P5 must be set to 0.	

(1) Lock detector works by using phase error pulse at the phase detector. Lock flag (FL) is set or reset according to this pulse-width disciminator. Hence, instability of the PLL may cause the lock detection circuit to malfunction. To stablize the PLL, it is required to evaluate application circuit in various condition of loop-gain (loop filter, CP current) and to verify under operation of the actual application.

A2	A1	A0	VOLTAGE APPLIED ON ADC INPUT
1	0	0	0.6 V_{CC} to V_{CC}
0	1	1	0.45 V_{CC} to 0.6 V_{CC}
0	1	0	0.3 V _{CC} to 0.45 V _{CC}
0	0	1	0.15 V _{CC} to 0.3 V _{CC}
0	0	0	0 V to 0.15 V _{CC}

Table 11. ADC Level⁽¹⁾

(1) Accuracy is $0.03 \times V_{CC}$.

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Example I²C Data Write Sequences

Telegram examples: Start - ADB - DB1 - DB2 - CB1 - BB - CB2 - Stop Start - ADB - DB1 - DB2 - Stop Start - ADB - CB1 - BB - CB2 - Stop Start - ADB - CB1 - BB - Stop Start - ADB - CB2 - Stop

Abbreviations:

ADB: Address byte BB: Band switch byte CB1: Control byte 1 CB2: Control byte 2 DB1: Divider byte 1 DB2: Divider byte 2 Start: Start condition Stop: Stop condition

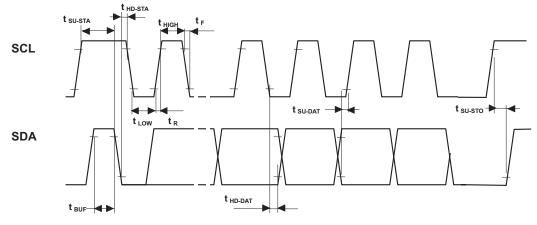


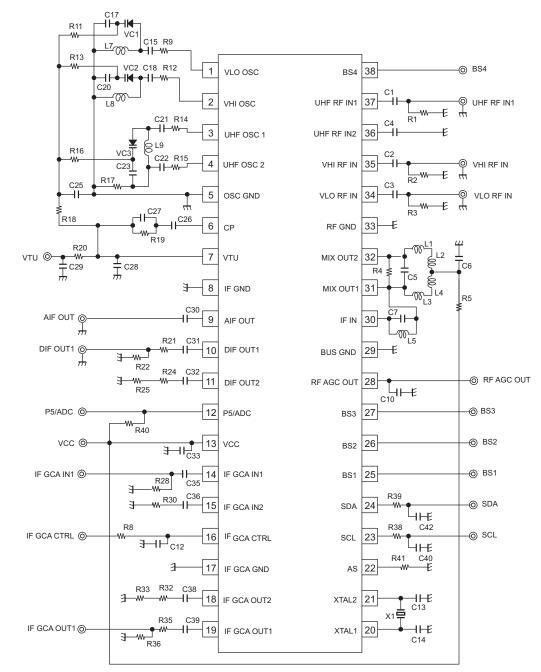
Figure 23. I²C Timing

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APPLICATION INFORMATION



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Figure 24. Reference Measurement Circuit

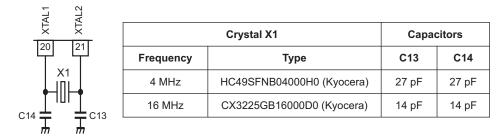


Figure 25. Reference Crystal Oscillation Circuit

Table 12	Component	Values for	Measurement	Circuit
----------	-----------	------------	-------------	---------

PART NAME	VALUE	PART NAME	VALUE
C1 (UHF RFIN1)	2.2nF	R1 (UHF RFIN1)	Open (51Ω)
C2 (VHI RFIN)	2.2nF	R2 (VHI RFIN)	Open (51Ω)
C3 (VLO RFIN)	2.2nF	R3 (VLO RFIN)	Open (51Ω)
C4 (UHF RFIN)	2.2nF	R4 (MIXOUT)	Open
C5 (MIXOUT)	5.5pF	R5 (MIXOUT)	Ω0
C6 (MIXOUT)	2.2nF	R8 (IF GCA CTRL)	0Ω
C7 (IF IN)	0Ω	R9 (VLO OSC)	Ω0
C10 (RF AGC OUT)	0.15µF	R11 (VLO OSC)	3.3kΩ
C12 (IF GCA CTRL)	0.1µF	R12 (VHI OSC)	10Ω
C13 (XTAL2)	27pF	R13 (VHI OSC)	3.3kΩ
C14 (XTAL1)	27pF	R14 (UHF OSC)	4.7Ω
C15 (VLO OSC)	4pF	R15 (UHF OSC)	4.7Ω
C17 (VLO OSC)	68pF	R16 (UHF OSC)	1kΩ
C18 (VHI OSC)	10pF	R17 (UHF OSC)	2.2kΩ
C20 (VHI OSC)	130pF	R18 (VTU)	3.3kΩ
C21 (UHF OSC)	6pF	R19 (CP)	82kΩ
C22 (UHF OSC)	6pF	R20 (VTU)	22kΩ
C23 (UHF OSC)	20pF	R21 (DIF OUT1)	200Ω
C25 (VTU)	2.2nF/50V	R22 (DIF OUT1)	Open
C26 (CP)	3.9nF/50V	R24 (DIF OUT2)	200Ω
C27 (CP)	10pF/50V	R25 (DIF OUT2)	51Ω
C28 (VTU)	150pF/50V	R28 (IF GCA IN1)	(51Ω)
C29 (VTU)	2.2nF/50V	R30 (IF GCA IN2)	(0Ω)
C30 (AIF OUT)	2.2nF	R32 (IF GCA OUT2)	200Ω
C31 (DIF OUT1)	2.2nF	R33 (IF GCA OUT2)	51Ω
C32 (DIF OUT2)	2.2nF	R35 (IF GCA OUT1)	200Ω
C33 (VCC)	0.1µF	R36 (IF GCA OUT1)	Open
C35 (IF GCA IN1)	2.2nF	R38 (SCL)	330Ω
C36 (IF GCA IN2)	2.2nF	R39 (SDA)	330Ω
C38 (IF GCA OUT2)	2.2nF	R40 (P5)	Open
C39 (IF GCA OUT1)	2.2nF	R41 (AS)	Open
C40 (SCL)	Open		
C42 (SDA)	Open	VC1 (VLO OSC)	KDV270E
		VC2 (VHI OSC)	KDV270E
		VC3 (UHF OSC)	KDV216E
		X1	4MHz crystal

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Table 12. Component Values for Measurement Circuit (continued)

	•
PART NAME	VALUE
L1 (MIXOUT)	470nH (LK1608R47KT Taiyo Yuden)
L2 (MIXOUT)	560nH (LK1608R56KT Taiyo Yuden)
L3 (MIXOUT)	470nH (LK1608R47KT Taiyo Yuden)
L4 (MIXOUT)	560nH (LK1608R56KT Taiyo Yuden)
L5 (IFIN)	Open
L7 (VLO OSC)	φ3.0mm, 9T, wire0.32mm
L8 (VHI OSC)	φ1.8mm, 4T, wire0.4mm
L9 (UHF OSC)	φ1.8mm, 2T, wire0.4mm

IF frequency: Local frequency range: 36 MHz VHF-LOW: 87 to 186 MHz VHF-HIGH: 193 to 462 MHz UHF: 470 to 894 MHz



Test Circuits

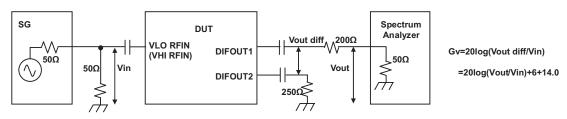


Figure 26. VHF Conversion Gain Measurement Circuit (at DIFOUT)

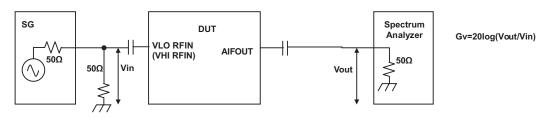


Figure 27. VHF Conversion Gain Measurement Circuit (at AIFOUT)

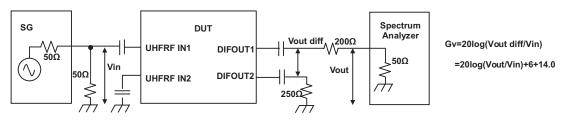
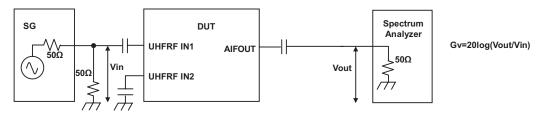


Figure 28. UHF Conversion Gain Measurement Circuit (at DIFOUT)





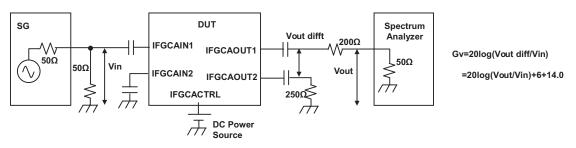


Figure 30. IF GCA Gain Measurement Circuit

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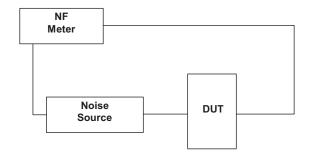


Figure 31. Noise Figure Measurement Circuit

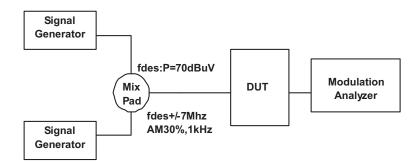


Figure 32. 1% Cross Modulation Distortion Measurement Circuit

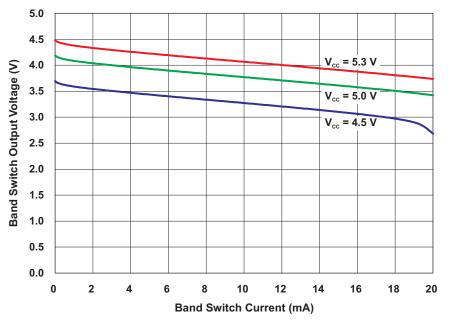
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TYPICAL CHARACTERISTICS

Band Switch Driver Output Voltage (BS1-BS4)





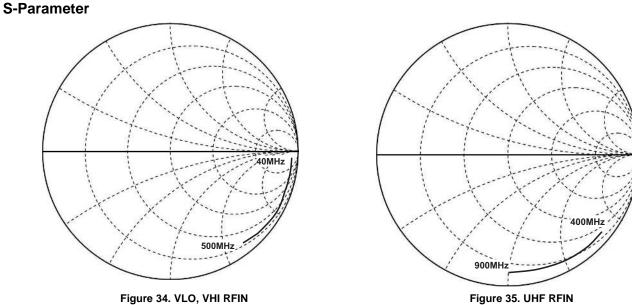
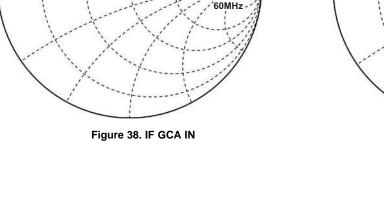


Figure 35. UHF RFIN





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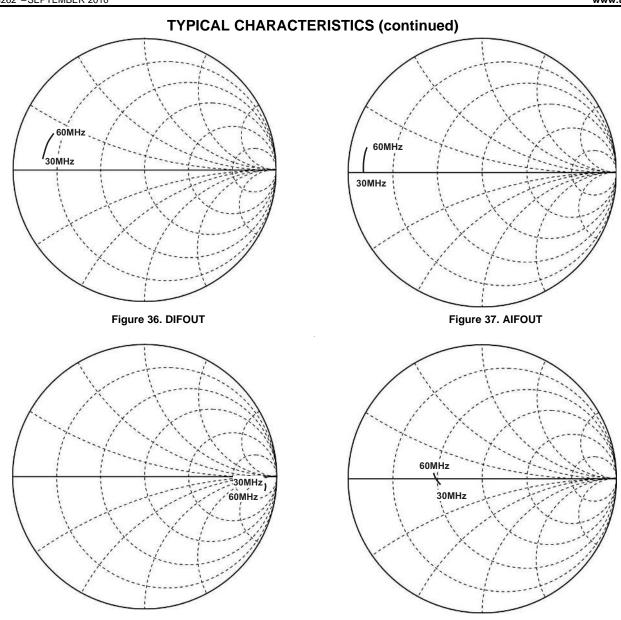


Figure 39. IF GCAOUT



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TYPICAL CHARACTERISTICS (continued)

IF GCA Gain vs Control Voltage

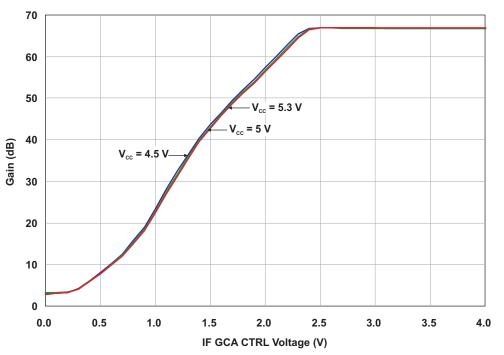


Figure 40. IF GCA Gain vs Control Voltage



10-Oct-2013

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)		(3)		(4/5)	
SN761645DBTR	OBSOLETE	TSSOP	DBT	38		TBD	Call TI	Call TI	-20 to 85	B1645	

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

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OBSOLETE: TI has discontinued the production of the device.

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⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

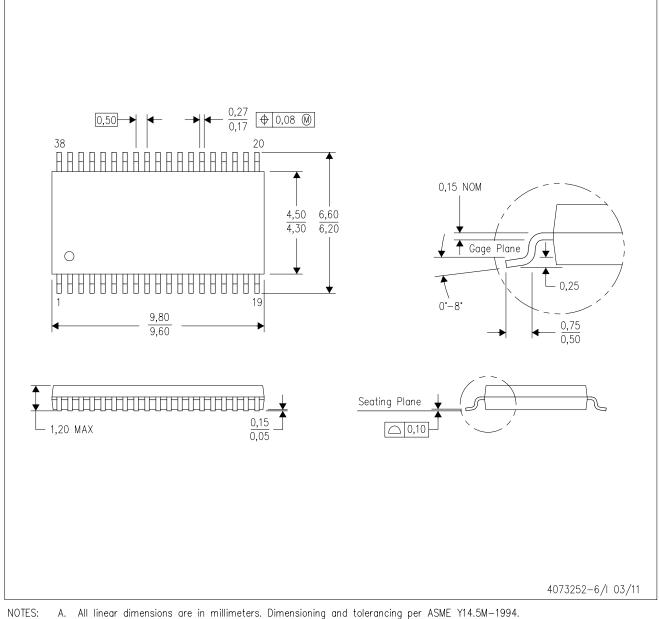
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